

N-Channel 150 V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}$ (Ω)	I _D (A)		
150	0.022 at V _{GS} = 10 V	60		
150	$0.027 \text{ at V}_{GS} = 4.5 \text{ V}$	50		

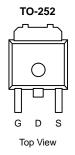
FEATURES

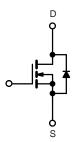
- DT-Trench Power MOSFET
- 175 °C Junction Temperature
- 100 % R_g Tested



APPLICATIONS

· Primary Side Switch





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)							
Parameter		Symbol	Limit	Unit			
Drain-Source Voltage		V _{DS}	150	V			
Gate-Source Voltage		V _{GS}	± 20				
Continuous Dunis Comment /T 475 90\h	$T_C = 25 ^{\circ}\text{C}$ $T_C = 125 ^{\circ}\text{C}$,	60				
Continuous Drain Current (T _J = 175 °C) ^b	T _C = 125 °C	l _D	42.2				
Pulsed Drain Current		I _{DM}	150	А			
Continuous Source Current (Diode Conduction)	I _S	60					
Avalanche Current	I _{AR}	36					
Repetitive Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E _{AR}	180	mJ			
Mayimum Dayyar Dissination	T _C = 25 °C	В	178 ^b	W			
Maximum Power Dissipation	T _A = 25 °C	P _D	8.0 ^a] vv			
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 175	°C				

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
hungtion to Ambient	t ≤ 10 s	- R _{thJA}	13	18	°C/W		
Junction-to-Ambient ^a	Steady State		39	50			
Junction-to-Case		R _{thJC}	0.5	0.9			

Notes:

- a. Surface mounted on 1" x 1" FR4 board.
- b. See SOA curve for voltage derating.



Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static					l		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	150	150		V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.2		3.0	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V _{DS} = 150 V, V _{GS} = 0 V			1	μA	
Zero Gate Voltage Drain Current	I_{DSS}	V _{DS} = 150 V, V _{GS} = 0 V, T _J = 125 °C			50		
		V _{DS} = 150 V, V _{GS} = 0 V, T _J = 175 °C			250		
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	60			Α	
		V _{GS} = 10 V, I _D = 10 A		0.022	0.027		
D : 0	D	V _{GS} = 10 V, I _D = 10 A, T _J = 125 °C		0.028	0.028		
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 10 A, T _J = 175 °C		0.032		Ω	
		V _{GS} = 4.5 V, I _D = 10 A		0.027			
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 10 A		52		S	
Dynamic ^a							
Input Capacitance	C _{iss}			2420		pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		155			
Reverse Transfer Capacitance	C _{rss}			10			
Total Gate Charge ^c	Q_g			28	38		
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 75 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 10 \text{ A}$		5.5		nC	
Gate-Drain Charge ^c	Q_{gd}			5			
Gate Resistance	R_g		1		3.2	Ω	
Turn-On Delay Time ^c	t _{d(on)}			9	15		
Rise Time ^c	t _r	$V_{DD} = 75 \text{ V}, R_L = 5 \Omega$		10	15	no	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_G = 2.5$		25	45	ns	
Fall Time ^c	t _f	Ω		10	24		
Source-Drain Diode Ratings and Cha	racteristic (T	C = 25 °C)					
Pulsed Current	I _{SM}				150	Α	
Diode Forward Voltage ^b	V_{SD}	I _F = 10 A, V _{GS} = 0 V		0.9	1.5	V	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 10 A, dI/dt = 100 A/μs		85	99	ns	

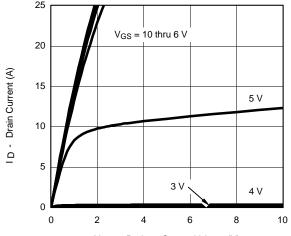
Notes:

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

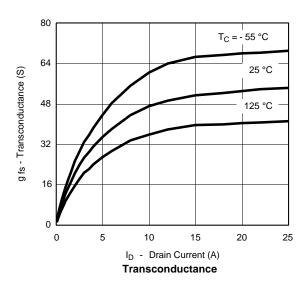


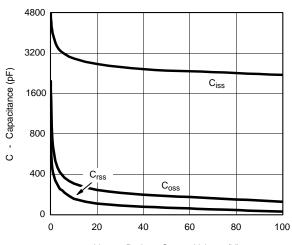
TYPICAL CHARACTERISTICS (25 °C unless noted)



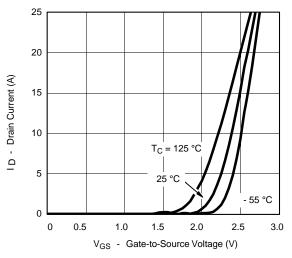
 $V_{\mbox{\footnotesize{DS}}}$ - Drain-to-Source Voltage (V)



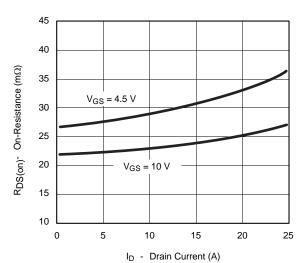




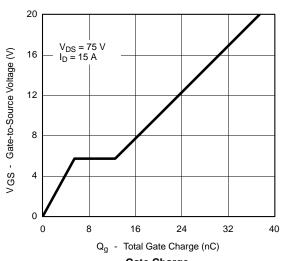
V_{DS} - Drain-to-Source Voltage (V) **Capacitance**



Transfer Characteristics



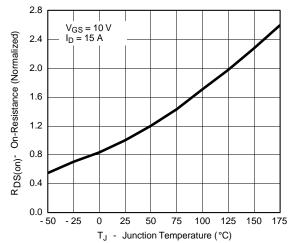
On-Resistance vs. Drain Current



Gate Charge

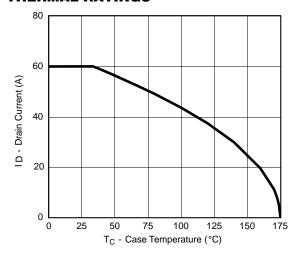


TYPICAL CHARACTERISTICS (25 °C unless noted)

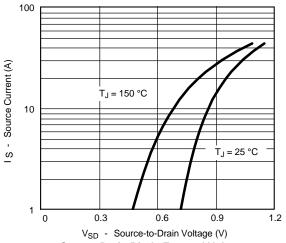


On-Resistance vs. Junction Temperature

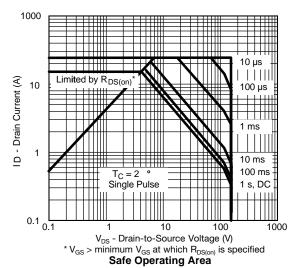
THERMAL RATINGS



Maximum Avalanche Drain Current vs. Case Temperature



Source-Drain Diode Forward Voltage



vs. Case Temperature

2
1
Duty Cycl = .5

0.2

0.1

0.05

10-4

10-3

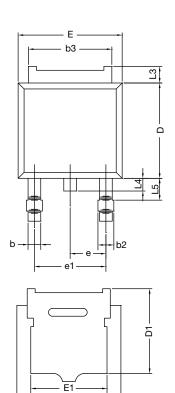
10-2

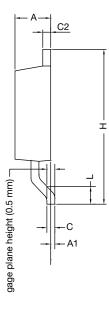
Square Wave Pulse Duration (sec)

Normalized Thermal Transient Impedance, Junction-to-Case



TO-252AA CASE OUTLINE





	MILLIMETERS		INC	HES		
DIM.	MIN.	MAX.	MIN.	MAX.		
Α	2.18	2.38	0.086	0.094		
A1	-	0.127	-	0.005		
b	0.64	0.88	0.025	0.035		
b2	0.76	1.14	0.030	0.045		
b3	4.95	5.46	0.195	0.215		
С	0.46	0.61	0.018	0.024		
C2	0.46	0.89	0.018	0.035		
D	5.97	6.22	0.235	0.245		
D1	5.21	-	0.205	-		
Е	6.35	6.73	0.250	0.265		
E1	4.32	-	0.170	-		
Н	9.40	10.41	0.370	0.410		
е	2.28 BSC		SC 0.090 BSC			
e1	4.56	BSC	0.180 BSC			
L	1.40	1.78	0.055	0.070		
L3	0.89	1.27	0.035	0.050		
L4	-	1.02	-	0.040		
L5	1.14	1.52	0.045	0.060		
ECN: X12-0247-Rev. M, 24-Dec-12						

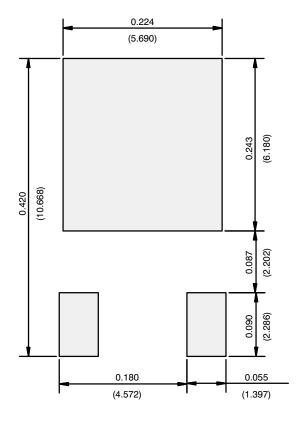
DWG: 5347

Note

• Dimension L3 is for reference only.



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Din-Tek Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Din-Tek"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Din-Tek makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Din-Tek disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Din-Tek's knowledge of typical requirements that are often placed on Din-Tek products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Din-Tek's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Din-Tek products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Din-Tek product could result in personal injury or death. Customers using or selling Din-Tek products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Din-Tek personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Din-Tek. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Din-Tek Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Din-Tek documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Din-Tek Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Din-Tek documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.